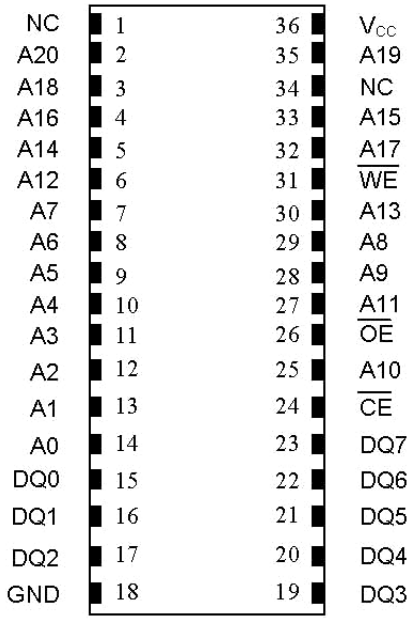
DS1270Y/AB
16M Nonvolatile SRAM

FEATURES

- 5 years minimum data retention in the absence of external power
- Data is automatically protected during power loss
- Unlimited write cycles
- Low-power CMOS operation
- Read and write access times as fast as 70ns
- Lithium energy source is electrically disconnected to retain freshness until power is applied for the first time
- Full ±10% Vcc operating range (DS1270Y)
- Optional ±5% Vcc operating range (DS1270AB)
- Optional industrial temperature range of -40℃ to +85℃, designated IND

PIN ASSIGNMENT



36-Pin ENCAPSULATED PACKAGE

740-mil EXTENDED

PIN DESCRIPTION

A0-A20	-Address Inputs
DQ0-DQ7	-Data In/Data Out
CE	-Chip Enable
WE	-Write Enable
OE	-Output Enable
Vcc	-Power (+5V)
GND	-Ground
NC	-No Connect

DESCRIPTION

The DS1270 16M Nonvolatile SRAMS are 16,777,216-bit, fully static nonvolatile SRAMs organized as 2,097,152 words by 8 bits. Each SRAM has a self-contained lithium energy source and control circuitry which constantly monitors Vcc for an out-of-tolerance condition. When such a condition occurs, the lithium energy source is automatically switched on and write protection is unconditionally enabled to prevent data corruption. There is no limit on the number of write cycles which can be executed and no additional support circuitry is required for microprocessor interfacing.

READ MODE

The DS1270 devices execute a read cycle whenever $\overline{WE}$ (Write Enable) is inactive (high) and $\overline{CE}$ (Chip Enable) and $\overline{OE}$ (Output Enable) are active (low). The unique address specified by the 21 address inputs (A0 –A20) defines which of the 2,097,152 bytes of data is accessed. Valid data will be available to the eight data output drivers within t_{ACC} (Access Time) after the last address input signal is stable, providing that $\overline{CE}$ and $\overline{OE}$ (Output Enable) access times are also satisfied. If $\overline{OE}$ and $\overline{CE}$ access times are not satisfied, then data access must be measured from the later-occurring signal ($\overline{CE}$ or $\overline{OE}$) and the limiting parameter is either t_{CO} for $\overline{CE}$ or t_{OE} for $\overline{OE}$ rather than t_{ACC}.

WRITE MODE

The DS1270 devices execute a write cycle whenever $\overline{WE}$ and $\overline{CE}$ signals are active (low) after address inputs are stable. The later-occurring falling edge of $\overline{CE}$ or $\overline{WE}$ will determine the start of the write cycle. The write cycle is terminated by the earlier rising edge of $\overline{CE}$ or $\overline{WE}$. All address inputs must be kept valid throughout the write cycle. $\overline{WE}$ must return to the high state for a minimum recovery time (t_{WR}) before another cycle can be initiated. The $\overline{OE}$ control signal should be kept inactive (high) during write cycles to avoid bus contention. However, if the output drivers are enabled ($\overline{CE}$ and $\overline{OE}$ active) then $\overline{WE}$ will disable the outputs in t_{ODW} from its falling edge.

DATA RETENTION MODE

The DS1270AB provides full-functional capability for Vcc greater than 4.75 volts and write protects by 4.5 volts. The DS1270Y provides full-functional capability for Vcc greater than 4.5 volts and write protects by 4.25 volts. Data is maintained in the absence of Vcc without any additional support circuitry. The nonvolatile static RAMs constantly monitor Vcc. Should the supply voltage decay, the NV SRAMs automatically write protect themselves, all inputs become don't care, and all outputs become high impedance. As Vcc falls below approximately 3.0 volts, a power switching circuit connects the lithium energy source to RAM to retain data. During power-up, when Vcc rises above approximately 3.0 volts, the power switching circuit connects external Vcc to RAM and disconnects the lithium energy source. Normal RAM operation can resume after Vcc exceeds 4.75 volts for the DS1270AB and 4.5 volts for the DS1270Y.

FRESHNESS SEAL

Each DS1270 device is shipped from ARTSCHIP Semiconductor with its lithium energy source disconnected, guaranteeing full energy capacity. When Vcc is first applied at a level greater than V_{TP}, the lithium energy source is enabled for battery backup operation.

ABSOLUTE MAXIMUM RATINGS *

Voltage on Any Pin Relative to Ground	-0.3V to +6V
Operating Temperature	0℃ to 70℃; -40℃ to +85℃ for IND parts
Storage Temperature	-40℃ to +70℃; -40℃ to +85℃ for IND parts
Soldering Temperature	260℃ for 10 seconds

*This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation sections of this specification if not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS (t_A: See Note 10)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
DS1270AB Power Supply Voltage	Vcc	4.75	5.0	5.25	V	
DS1270Y Power Supply Voltage	Vcc	4.5	5.0	5.5	V	
Logic 1 Input Voltage	V_{IH}	2.2		Vcc	V	
Logic 0 Input Voltage	V_{IL}	0		+0.8	V	

DC ELECTRICLA CHARACTERISTICS (Vcc =5V±5% for DS1270AB) (t_A: See Note 10)(Vcc=5V ±10% for DS1270Y)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Input Leakage Current	I_{IL}	-4.0		+4.0	µA	
I/O Leakage Current	I_{IO}	-4.0		+4.0	µA	
Output Current @2.4V	I_{OH}	-1.0			mA	
Output Current @ 0.4V	I_{OL}	2.0			mA	
Standby Current $\overline{CE}$=2.2V	I_{CCS1}		1.0	1.5	mA	
Standby Current $\overline{CE}$=Vcc-0.5V	I_{CCS2}		100	250	µA	
Operating Current	I_{CCO1}			85	mA	
Write Protection Voltage (DS1270AB)	V_{TP}	4.50	4.62	4.75	V	
Write Protection Voltage (DS1270Y)	V_{TP}	4.25	4.37	4.5	V	

CAPACITANCE (t_A=25°C)

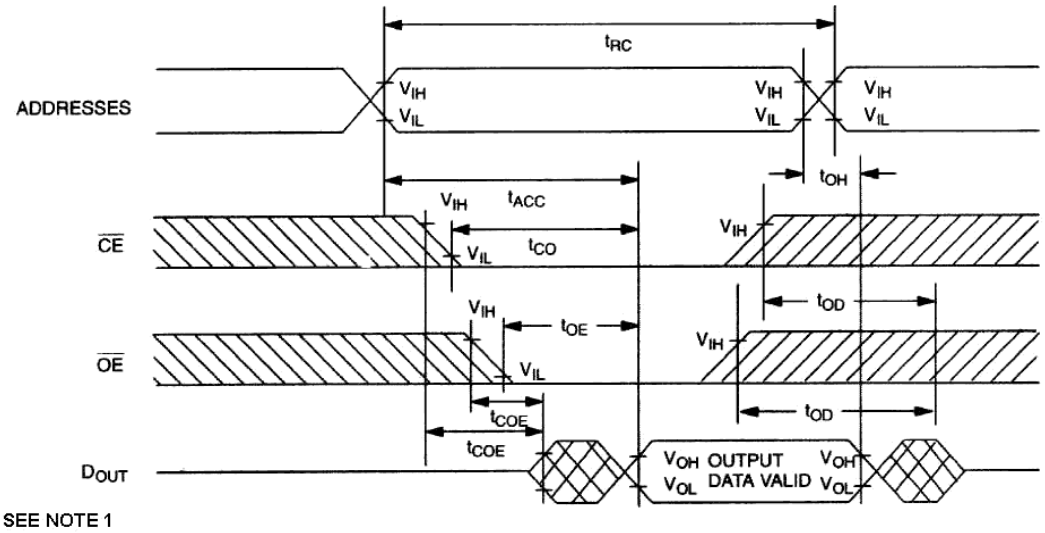
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Input Capacitance	C_{IN}		20	40	pF	
Output Capacitance	$C_{I/O}$		20	40	pF	

AC ELECTRICAL CHARACTERISTICS

(Vcc = 5V ±5% for DS1270AB)
(t_A:See Note 10) (Vcc=5V ± 10% for DS1270Y)

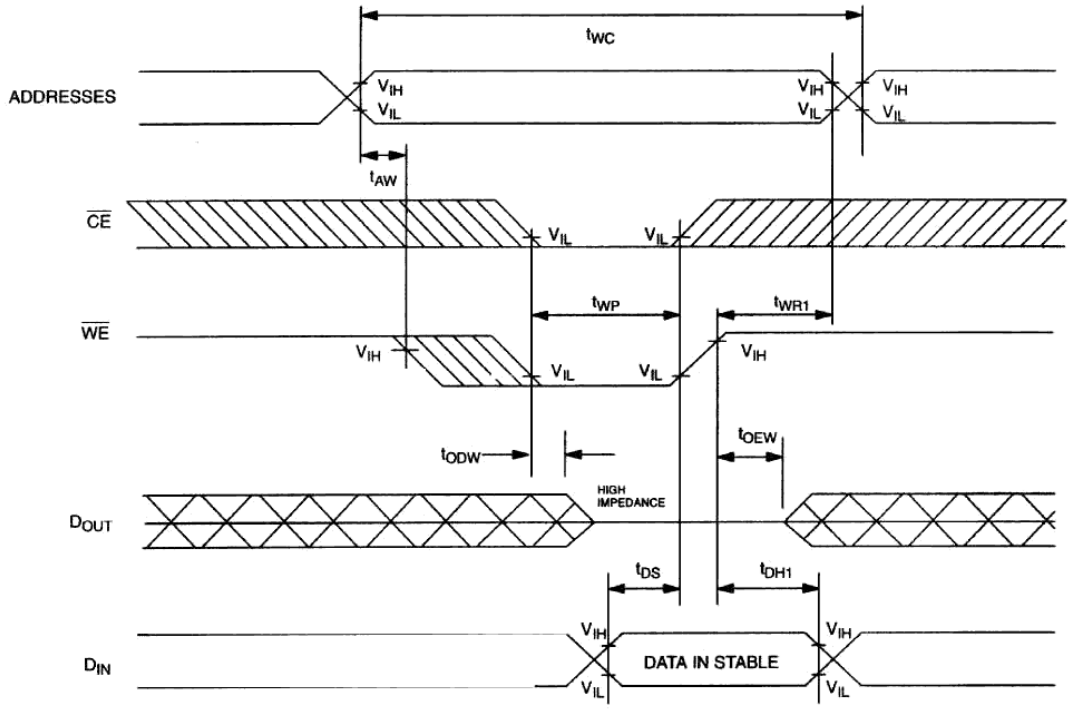
PARAMETER	SYMBOL	DS1270AB-70 DS1270Y-70		DS1270AB-100 DS1270Y-100		UNITS	NOTES
		MIN	MAX	MIN	MAX		
Read Cycle Time	t_{RC}	70		100		ns	
Access Time	t_{ACC}		70		100	ns	
$\overline{OE}$ to Output Valid	t_{OE}		35		50	ns	
$\overline{CE}$ to Output Valid	t_{CO}		70		100	ns	
$\overline{OE}$ or $\overline{CE}$ to Output Active	t_{COE}	5		5		ns	5
Output High Z from Deselection	t_{OD}		25		35	ns	5
Output Hold from Address Change	t_{OH}	5		5		ns	
Write Cycle Time	t_{WC}	70		100		ns	
Write Pulse Width	t_{WP}	55		75		ns	3
Address Setup Time	t_{AW}	0		0		ns	
Write Recovery Time	t_{WR1} t_{WR2}	5 15		5 15		ns ns	12 13
Output High Z from $\overline{WE}$	t_{ODW}		25		35	ns	5
Output Active from $\overline{WE}$	t_{OEW}	5		5		ns	5
Data Setup Time	t_{DS}	30		40		ns	4
Data Hold Time	t_{DH1} t_{DH2}	0 10		0 10		ns ns	12 13

TIMING DIAGRAM: READ CYCLE



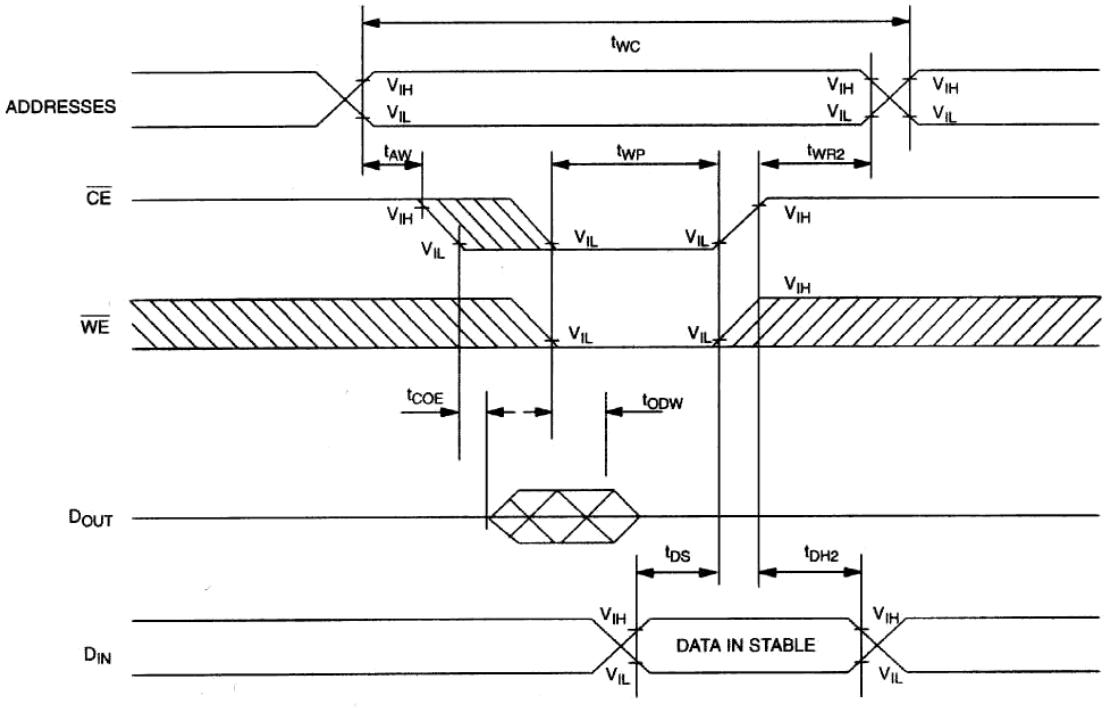
SEE NOTE 1

TIMING DIAGRAM: WRITE CYCLE 1



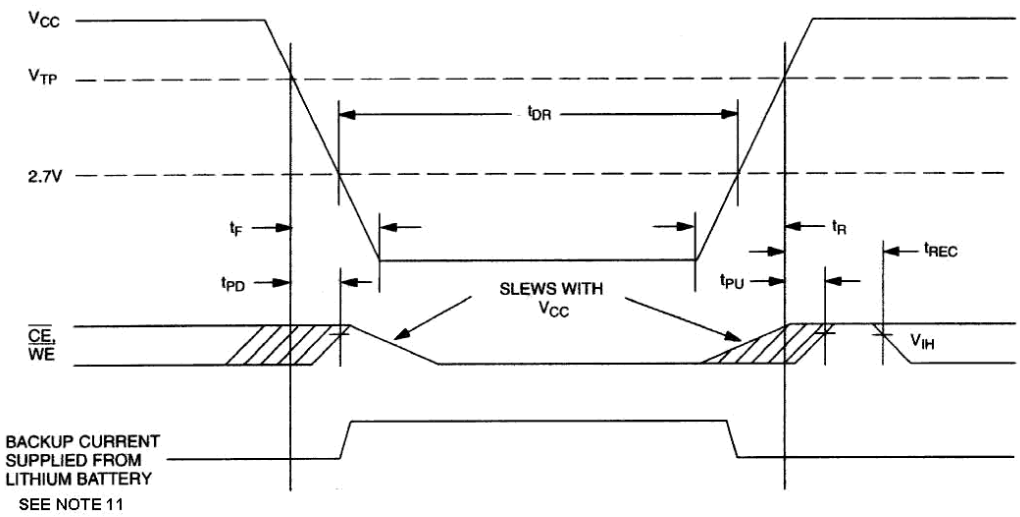
SEE NOTES 2, 3, 4, 6, 7, 8, and 12

TIMING DIAGRAM: WRITE CYCLE 2



SEE NOTES 2, 3, 4, 6, 7, 8 AND 13

POWER-DOWN/POWER-UP CONDITION



POWER-DOWN/POWER-UP TIMING (t_A:See Note 10)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Vcc Fail Detect to $\overline{CE}$ and $\overline{WE}$ Inactive	t_{PD}			1.5	µs	11
Vcc slew from V_{TP} to 0V	t_F	150			µs	
Vcc slew from 0V to V_{TP}	t_R	150			µs	
Vcc Valid to $\overline{CE}$ and $\overline{WE}$ Inactive	t_{PU}			2	ms	
Vcc Valid to End of Write Protection	t_{REC}			125	ms	

(tA=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Expected Data Retention Time	t_{DR}	5			years	9

WARNING:

Under no circumstance are negative undershoots, of any amplitude, allowed when device is in battery backup mode.

NOTES:

1. $\overline{WE}$ is high for a read cycle.
2. $\overline{OE}$ = V_{IH} or V_{IL}. If $\overline{OE}$ = V_{IH} during write cycle, the output buffers remain in a high-impedance state.
3. t_{WP} is specified as the logical AND of $\overline{CE}$ and $\overline{WE}$. t_{WP} is measured from the latter of $\overline{CE}$ or $\overline{WE}$ going low to the earlier of $\overline{CE}$ or $\overline{WE}$ going high.
4. t_{DS} is measured from the earlier of $\overline{CE}$ or $\overline{WE}$ going high.
5. These parameters are sampled with a 5pF load and are not 100% tested.
6. if the $\overline{CE}$ low transition occurs simultaneously with or latter than the $\overline{WE}$ low transition, the output buffers remain in a high-impedance state during this period.
7. If the $\overline{CE}$ high transition occurs prior to or simultaneously with the $\overline{WE}$ high transition, the output buffers remain in high-impedance state during this period.
8. If $\overline{WE}$ is low or the $\overline{WE}$ low transition occurs prior to or simultaneously with the $\overline{CE}$ low transition, the output buffers remain in a

high-impedance state during this period.

9. Each DS1270 has a built-in switch that disconnects the lithium source until the user first applies Vcc. The expected t_{DR} is defined as accumulative time in the absence of Vcc starting from the time power is first applied by the user. This parameter is assured by component selection, process control, and design. It is not measured directly during production testing.
10. All AC and DC electrical characteristics are valid over the full operating temperature range. For commercial products, this range is 0℃ to 70℃. For industrial products (IND), this range is -40℃ to +85℃.
11. In a power-down condition the voltage on any pin may not exceed the voltage on Vcc.
12. t_{WR1} and t_{DH1} are measured from $\overline{WE}$ going high.
13. t_{WR2} and t_{DH2} are measured from $\overline{CE}$ going high.
14. DS1270 modules are recognized by underwriters Laboratory (U.L.®) under file E99151.

DC TEST CONDITIONS

Outputs Open

Cycle =200ns for operating current

All voltages are referenced to ground

AC TEST CONDITIONS

Output Load:100pF +1TTL Gate

Input Pulse Levels:0.0 to 3.0 volts

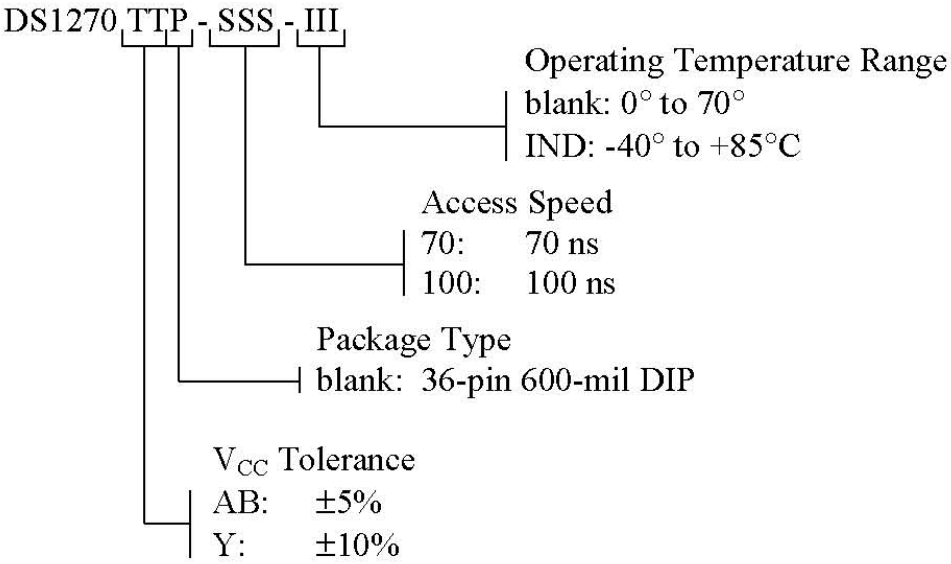
Timing Measurement Reference Levels

Input:1.5V

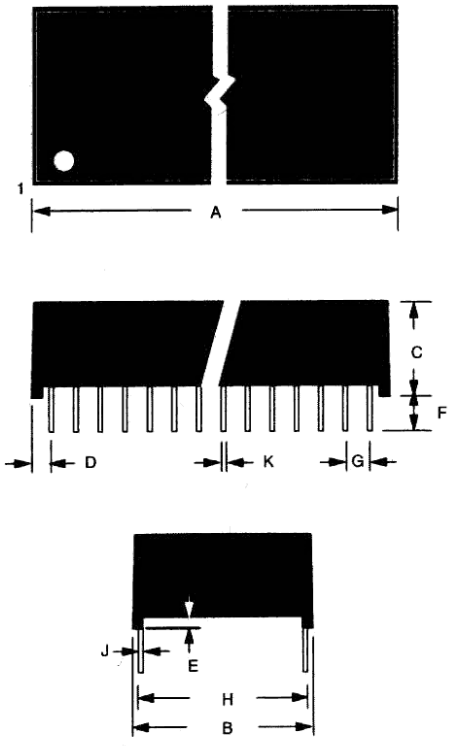
Output:1.5V

Input pulse Rise and Fall Times:5ns

ORDERING INFORMATION



DS1270Y/AB NONVOLATILE SRAM 36-PIN 740-MIL EXTENDED MODULE, LONG



PKG	36-PIN	
DIM	MIN	MAX
A IN.	2.080	2.100
MM	52.83	53.34
B IN.	0.720	0.740
MM	18.29	18.80
C IN.	0.395	0.405
MM	10.03	10.29
D IN.	0.180	0.210
MM	4.57	5.33
E IN.	0.015	0.025
MM	0.38	0.63
F IN.	0.120	0.150
MM	3.05	4.06
G IN.	0.090	0.110
MM	2.29	2.79
H IN.	0.590	0.630
MM	14.99	16.00
J IN.	0.008	0.012
MM	0.20	0.30
K IN.	0.015	0.021
MM	0.38	0.53